



SO2907AW

SMALL SIGNAL PNP TRANSISTOR

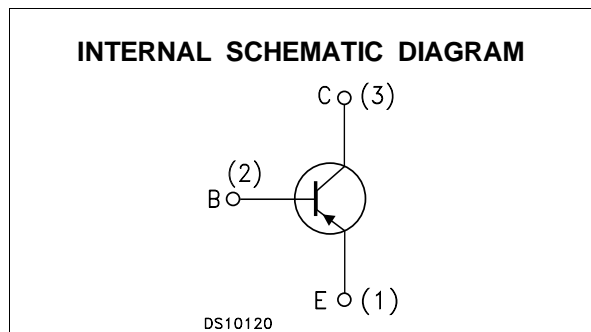
PRELIMINARY DATA

Type	Marking
SO2907AW	03W

- SILICON EPITAXIAL PLANAR PNP TRANSISTOR
- MINIATURE SOT-323 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE & REEL PACKING
- THE NPN COMPLEMENTARY TYPE IS SO2222AW

APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTOR WITH HIGH GAIN AND LOW SATURATION VOLTAGE



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Emitter Voltage ($I_E = 0$)	-60	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	-60	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	-5	V
I_C	Collector Current	-0.6	A
I_{CM}	Collector Peak Current ($t_p < 5$ ms)	-0.8	A
P_{tot}	Total Dissipation at $T_{amb} = 25$ °C	200	mW
T_{stg}	Storage Temperature	-65 to 150	°C
T_j	Max. Operating Junction Temperature	150	°C

SO2907AW

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	625	°C/W
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• Device mounted on a PCB area of 1 cm²

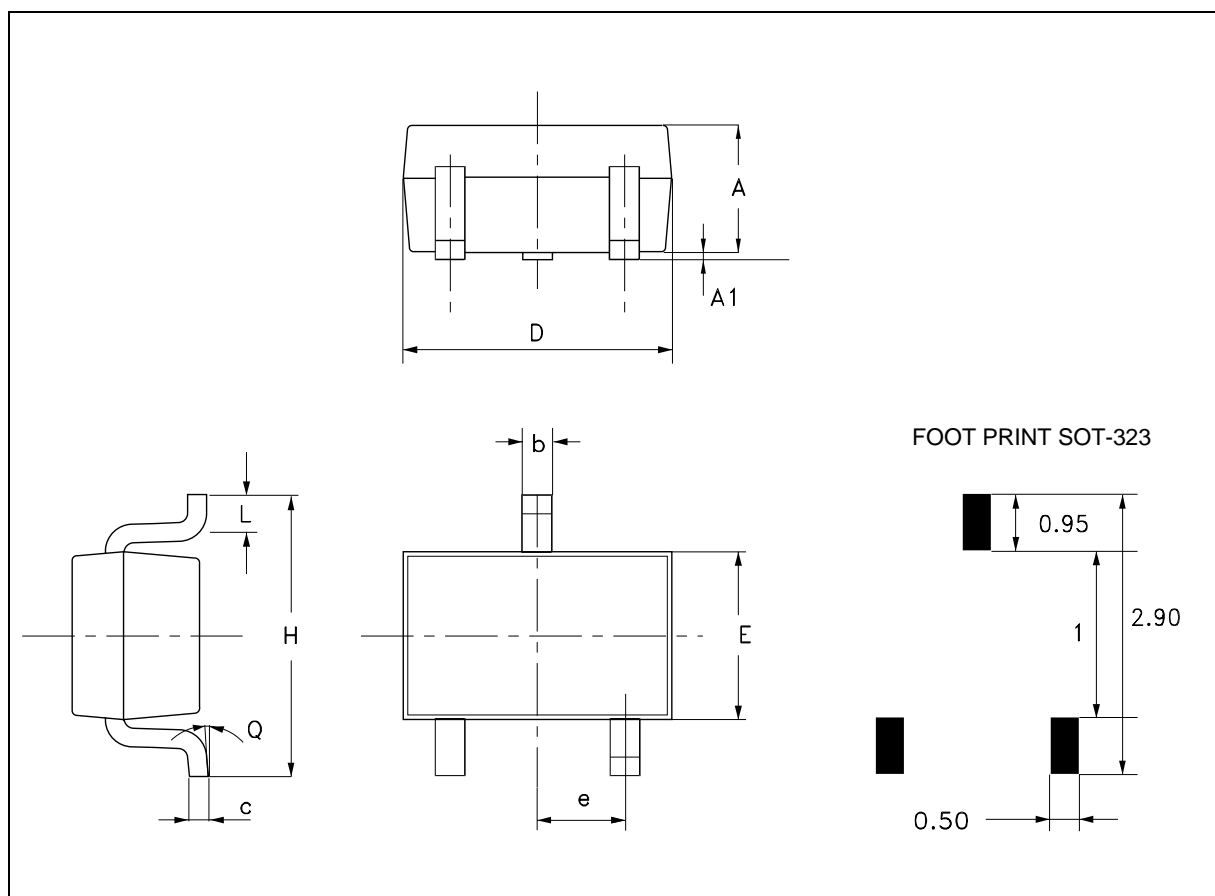
ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I _{CEX}	Collector Cut-off Current (V _{BE} = -3 V)	V _{CE} = -30 V			-50	nA
I _{BEX}	Base Cut-off Current (V _{BE} = -3 V)	V _{CE} = -30 V			-50	nA
I _{CBO}	Collector Cut-off Current (I _E = 0)	V _{CB} = -50 V			-10	nA
V _{(BR)CEO} *	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = -10 mA	-60			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = -10 μA	-60			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = -10 μA	-5			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage	I _C = -150 mA I _B = -15 mA I _C = -500 mA I _B = -50 mA			-0.4 -1.6	V V
V _{BE(sat)} *	Collector-Base Saturation Voltage	I _C = -150 mA I _B = -15 mA I _C = -500 mA I _B = -50 mA			-1.3 -2.6	V V
h _{FE} *	DC Current Gain	I _C = -0.1 mA V _{CE} = -10 V I _C = -1 mA V _{CE} = -10 V I _C = -10 mA V _{CE} = -10 V I _C = -150 mA V _{CE} = -10 V I _C = -500 mA V _{CE} = -10 V	75 100 100 100 50		300	
f _T	Transition Frequency	I _C = -50 mA V _{CE} = -20V f = 100MHz	200			MHz
C _{CBO}	Collector-Base Capacitance	I _E = 0 V _{CB} = -10 V f = 1 MHz			8	pF
C _{EBO}	Emitter-Base Capacitance	I _C = 0 V _{EB} = -2 V f = 1 MHz			30	pF
t _d	Delay Time	I _C = -150 mA I _B = -15 mA			10	ns
t _r	Rise Time	V _{CC} = -30V			40	ns
t _{on}	Switching On Time				45	ns
t _s	Storage Time	I _C = -150 mA I _{B1} = -I _{B2} = -15mA		190		ns
t _f	Fall Time	V _{CC} = -30V			30	ns
t _{off}	Switching Off Time			220		ns

* Pulsed: Pulse duration = 300 μs, duty cycle ≤ 2 %

SOT-323 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	0.8		1.1	0.031		0.043
A1	0		0.1	0		0.003
b	0.25		0.4	0.009		0.015
c	0.1		0.26	0.004		0.010
D	1.8	2.0	2.2	0.070	0.078	0.086
E	1.15	1.25	1.35	0.045	0.049	0.053
e		0.65			0.025	
H	1.8	2.1	2.4	0.070	0.082	0.094
L	0.1	0.2	0.3	0.004	0.007	0.011
Q	0		10°	0		10°



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